

**Vishay Siliconix** 

## 6-Ω, Low Voltage, Dual SPST Analog Switch

#### DESCRIPTION

The DG2737, DG2738 and DG2739 are high performance, low on-resistance analog switches of dual SPST configuration.

Built on Vishay Siliconix's sub-micro CMOS technology, the DG2737, DG2738, DG2739 achieve switch on-resistance of 6 Ω at 3 V V+. Its - 3 dB bandwidth is typically 720 MHz.

It can switch signals with amplitudes of up to  $V_{CC}$  to be transmitted in either direction.

Combining low power, high speed, low on-resistance and small physical size, the DG2737, DG2738, DG2739 are ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG2737, DG2738, DG2739 come in a small miniQFN-8 lead package (1.4 x 1.4 x 0.55 mm). As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations and is 100 % RoHS compliant.

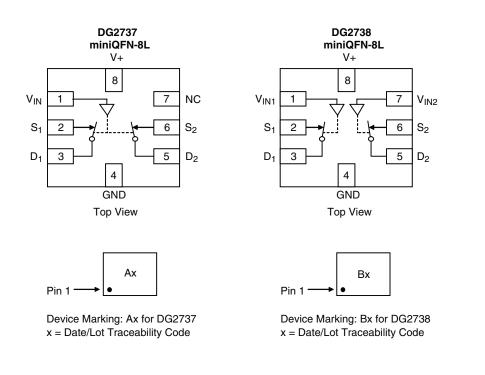
#### **FEATURES**

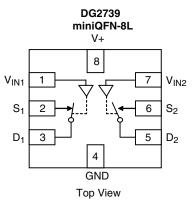
- Voltage range: 2.3 V to 4.3 V
- Low on-resistance: 6 Ω typ. at 3 V
- 48 dB crosstalk at 240 MHz
- Low power consumption
- Ultra small miniQFN8 package of 1.4 x 1.4 x 0.55 mm
- > 300 mA latch up current per JESD78
- Switch exceeds 5 kV ESD/HBM

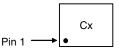




#### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION







Device Marking: Cx for DG2739 x = Date/Lot Traceability Code

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TRUTH TABLE 1					
Input	Logio	DG273			
Input	Logic	S <sub>1</sub> and D <sub>1</sub>	S <sub>2</sub> and D <sub>2</sub>		
N.	Low	ON	ON		
V <sub>IN</sub>	High	OFF	OFF		

TRUTH TABLE 2							
lanut	Logic	DG	2738	DG2739			
Input		S <sub>1</sub> and D <sub>1</sub>	S <sub>2</sub> and D <sub>2</sub>	S <sub>1</sub> and D <sub>1</sub>	S <sub>2</sub> and D <sub>2</sub>		
V <sub>IN1</sub>	Low	ON	X	ON	Х		
	High	OFF	X	OFF	Х		
V <sub>IN2</sub>	Low	Х	ON	Х	OFF		
	High	Х	OFF	Х	ON		

ORDERING INFORMATION					
Temp. Range	Package	Part Number			
- 40 °C to 85°C	miniQFN-8L	DG2737DN-T1-E4 DG2738DN-T1-E4 DG2739DN-T1-E4			

ABSOLUTE MAXIMUM RAT	INGS T <sub>A</sub> = 25 °C, unless o	therwise noted		
Parameter		Limit	Unit	
Reference to GND	V+	- 0.3 to 5.0	- V	
Reference to GND	V <sub>IN</sub> , D, S <sup>a</sup>	- 0.3 to (V+ + 0.3)		
Current (Any terminal except D or S)		30		
Continuous Current (D or S)		± 300	mA	
Peak Current (Pulsed at 1 ms, 10 % Duty Cycle)		± 500		
Storage Temperature (D Suffix)		- 65 to 150	°C	
Power Dissipation (Packages) <sup>b</sup>	miniQFN-8L <sup>c</sup>	190	mW	

Notes:

a. Signals on V<sub>IN</sub>, D, or S exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC board.

c. Derate 2.4 mW/°C above 70 °C.

SPECIFICATIONS V+ = 3 V							
		Test Conditions Unless Otherwise Specified		Limits - 40 °C to 85 °C			
Parameter	Symbol	$V_{+} = 3 V, V_{IN} = 0.4 V \text{ or } 1.4 V^{e}$	Temp. <sup>a</sup>	Min. <sup>b</sup>	Typ. <sup>c</sup>	Max. <sup>b</sup>	Unit
Analog Switch							
Analog Signal Range <sup>d</sup>	V <sub>analog</sub>	R <sub>ON</sub>	Full	0		V+	V
On-Resistance	D	$V_{+} = 3 V, I_{S} = 8 mA, V_{D} = 0.4 V$	Room		6	8	
On-nesistance	R <sub>ON</sub>	$v + = 3 v$ , $i_{S} = 0 mA$ , $v_{D} = 0.4 v$	Full			9	
R <sub>ON</sub> Match <sup>d</sup>	$\Delta R_{ON}$	$V+ = 3 V, I_S = 8 mA, V_D = 0.4 V$	Room		0.1	0.5	Ω
R <sub>ON</sub> Flatness <sup>d</sup>	R <sub>ON</sub> Flatness	$V + = 3 V, I_S = 8 mA, V_D = 0 V, 1 V$	Room		2.6	4	



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SPECIFICATIONS V+	= 3 V						
		Test Conditions Unless Otherwise Specified		<b>Limits</b> - 40 °C to 85 °C			
Parameter	Symbol	$V$ + = 3 V, $V_{IN}$ = 0.4 V or 1.4 $V^{e}$	Temp. <sup>a</sup>	Min. <sup>b</sup>	Typ. <sup>c</sup>	Max. <sup>b</sup>	Unit
Analog Switch							
			Room	- 10		10	
Switch Off Leakage	I <sub>S(off)</sub>	$V+ = 4.3 V, V_S = 0.3 V/3.3 V,$	Full	- 100		100	
Current		V <sub>D</sub> = 3.3 V/0.3 V	Room	- 10		10	nA
	I <sub>D(off)</sub>		Full	- 100		100	103
Channel-On Leakage Current		V+ = 4.3 V, V <sub>S</sub> = V <sub>D</sub> = 4 V/0.3 V	Room	- 10		10	
	I <sub>D(on)</sub>	v+ = +.0 v, vg = vD = + v/0.0 v	Full	- 100		100	
Digital Control	•		T		r		
Input High Voltage	V <sub>INH</sub>	V+ = 2.3 V to 4.3 V	Full	1.3			v
Input Low Voltage	V <sub>INL</sub>		Full			0.5	•
Input Current	$I_{INL}$ or $I_{INH}$	V <sub>IN</sub> = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics	•		T		r		
Turn-On Time <sup>e</sup>	t <sub>ON</sub>		Room		23	60	
	SON	V+ = 2.3 V to 3.6 V, $V_{NO}$ or $V_{S}$ = 1.5 V,	Full			70	ns
Turn-Off Time <sup>e</sup>	t <sub>OFF</sub>	$R_{L} = 50 \ \Omega, C_{L} = 35 \ pF$	Room		13	50	113
	-OFF		Full			60	
Break-Before-Make Time	t <sub>BBM</sub>	V+ = 2.3 V to 4.3 V	Room		6		ns
			Full	1			
Charge Injection <sup>d</sup>	Q	$C_L$ = 1 nF, $R_{GEN}$ = 0 $\Omega$ , $V_{GEN}$ = 0 V	Room		10.4		рС
		$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$			- 79		dB
Off-Isolation <sup>d</sup>	O <sub>IRR</sub>	$R_L$ = 50 Ω, $C_L$ = 5 pF, f = 10 MHz			- 59		
		$R_L = 50 \Omega$ , $C_L = 5 pF$ , f = 240 MHz	Room		- 28		
		$R_L$ = 50 Ω, $C_L$ = 5 pF, f = 1 MHz			- 109		42
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	$R_L$ = 50 Ω, $C_L$ = 5 pF, f = 10 MHz	_		- 99		1
1		$R_L = 50 \Omega$ , $C_L = 5 pF$ , f = 240 MHz			- 48		
3 dB bandwidth <sup>d</sup>		R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF	Room		720		MHz
Channel to Channel skew <sup>d</sup>					25		
Skew of Opposite Transitions of the Same Output <sup>d</sup>		$R_L$ = 50 Ω, $C_L$ = 5 pF	Room		20		ps
Total Jitter <sup>d</sup>					200		
Source Off Capacitance <sup>d</sup>	C <sub>S(off)</sub>	f = 1 MHz, V <sub>S</sub> = 0 V	Room		4.4		
Drain Off Capacitance <sup>d</sup>	C <sub>D(off)</sub>				3.8		pF
Drain On Capacitance <sup>d</sup>	C <sub>D(on)</sub>				10		
Control Pin Capacitanced	C <sub>IN</sub>	f = 1 MHz	Room		8.3		l
Power Supply							
Power Supply Range	V+			2.3		4.3	V
Power Supply Current	l+	V <sub>IN</sub> = 0 or V+	Full			1.0	μΑ

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

c. Typical values are for design aid only, not guaranteed nor subject to production testing.

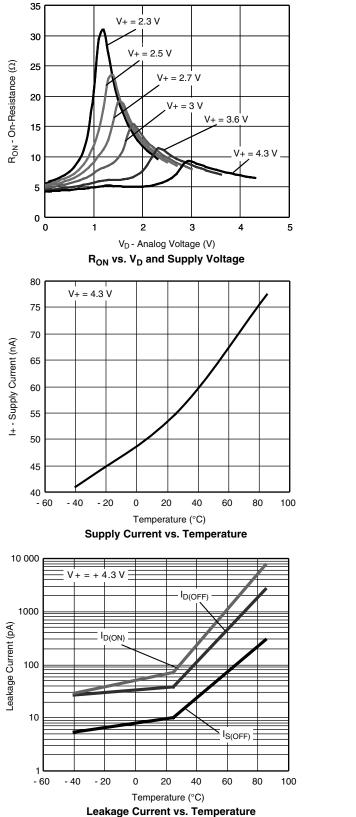
d. Guarantee by design, not subjected to production test.

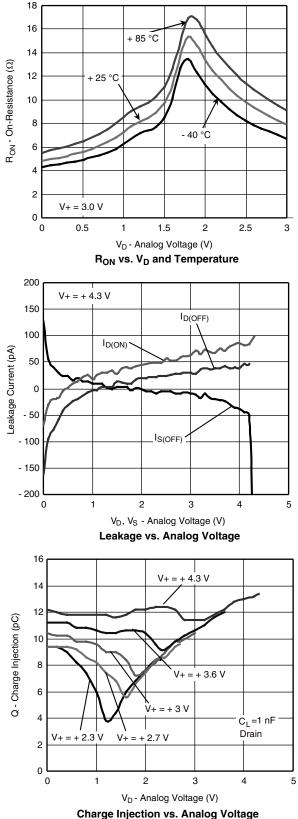
e. V<sub>IN</sub> = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



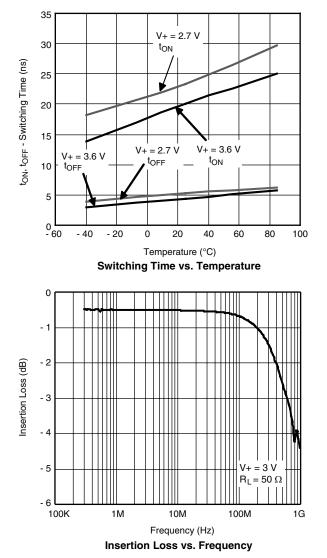


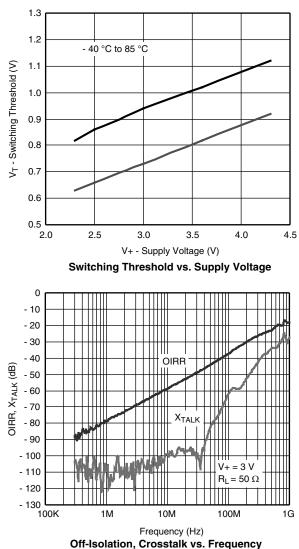
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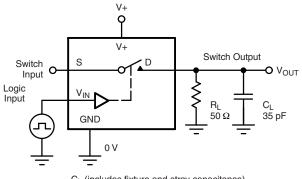


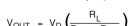


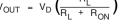


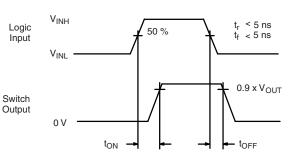
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#### **TEST CIRCUITS**

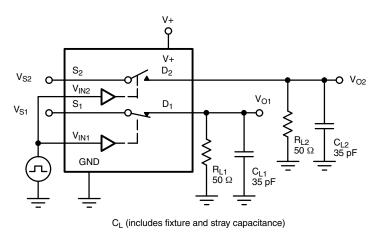








Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.



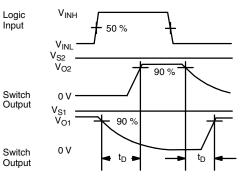
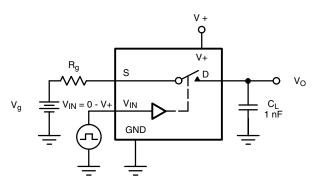
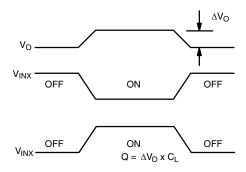
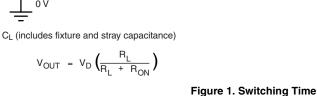


Figure 2. Break-Before-Make (DG2739)













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#### **TEST CIRCUITS**

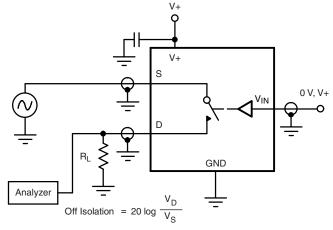
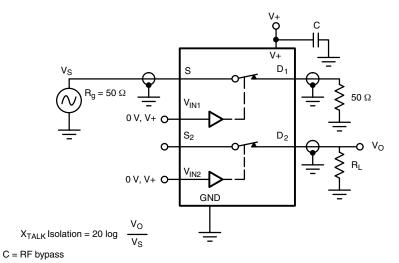
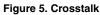


Figure 4. Off-Isolation





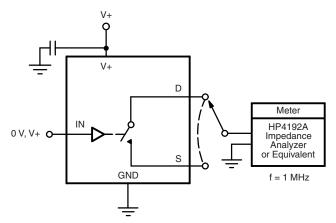


Figure 6. Channel Off/On Capacitance

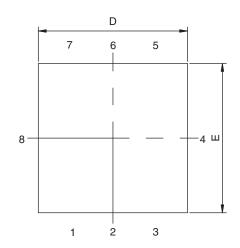
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?68801.

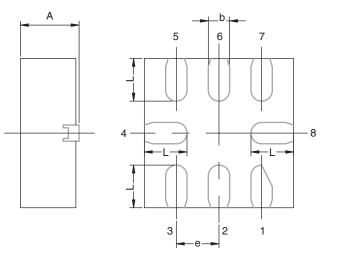


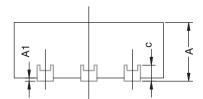
## Package Information

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#### MINIQFN-8L CASE OUTLINE



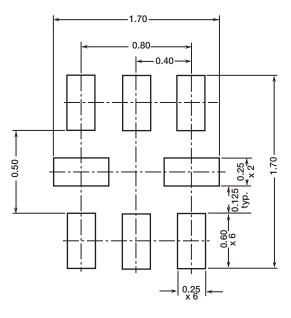




		MILLIMETERS			INCHES	
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	0.50	0.55	0.60	0.0197	0.0217	0.0236
A1	0.00	-	0.05	0.000	-	0.002
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.15 REF			0.006 REF		
D	1.35	1.40	1.45	0.053	0.055	0.057
E	1.35	1.40	1.45	0.053	0.055	0.057
е	0.40 BSC			0.016 BSC		
L	0.35	0.40	0.45	0.014	0.016	0.018
ECN: C-08336-Re DWG: 5964	ev. A, 05-May-08					



#### **RECOMMENDED MINIMUM PADS FOR MINI QFN 8L**



Suggested Minimum Pad Dimensions in mm



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